

Substitute for form 1449A/PTO

NOV 22 2004

Application Number

10/796,514

Filing Date

March 9, 2004

First Named Inventor

John P. Snyder

Art Unit

2711

Examiner Name

Not Yet Known

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

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of

7

Attorney Docket Number

14467.05

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	DOCUMENT NUMBER Number - Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
SK		US- 4,053,924	10-11-1977	Roman et al.	
SK		US- 4,300,152	11-10-1981	Lepselter	
SK		US- 4,485,550	12-4-1984	Koeneke et al.	
SK		US- RE32,613	2-23-1988	Lepselter et al.	
SK		US- 4,780,429	10-25-1988	Roche et al.	
SK		US- 4,942,441	7-17-1990	Konishi et al.	
SK		US- 5,079,182	1-7-1992	Ilderem et al.	
SK		US- 5,323,053	6-21-1994	Luryi et al.	
SK		US- 5,338,698	8-16-1994	Subbanna	
SK		US- 5,444,302	8-22-1995	Nakajima et al.	
SK		US- 5,663,584	9-2-1997	Welch	
SK		US- 5,760,449	6-2-1998	Welch	
SK		US- 5,767,557	6-16-1998	Kizilyalli	
SK		US- 5,801,398	9-1-1998	Hebiguchi	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	FOREIGN PATENT DOCUMENT		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	TRANSLATION	
		Country Code:	Number - Kind Code (if known)				YES	NO
SK		EP	0 603 102 A2	6-22-1994			<input checked="" type="checkbox"/>	<input type="checkbox"/>
SK		WO	01 45157	06-21-2001	Spinnaker Semiconductor, Inc.		<input type="checkbox"/>	<input type="checkbox"/>
SK		JP	06097109	04-08-1994	Fujitsu Ltd		<input type="checkbox"/>	<input checked="" type="checkbox"/>
SK		JP	2000124329	04-28-2000	Toshiba Corp.		<input type="checkbox"/>	<input checked="" type="checkbox"/>
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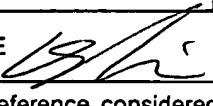
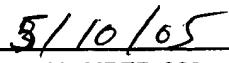
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SC		US- 5,883,010	3-16-1999	Merrill et al.	
SK		US- 6,037,605	3-14-2000	Yoshimura	
SP		US- 6,160,282	12-12-2000	Merrill	
SC		US- 6,268,636	7-31-2001	Welch	
SK		US- 6,303,479	10-16-2001	Snyder	
SC		US- 6,323,528	11-27-2001	Yamazaki et al.	
SC		US- 6,353,251	3-5-2002	Kimura	
SC		US- 6,413,829	7-2-2002	Yu	
SK		US- 6,420,742	7-16-2002	Ahn et al.	
SK		US- 6,486,080	11-26-2002	Chooi et al.	
SK		US- 6,495,882	12-17-2002	Snyder	
SK		US- 6,509,609	1-21-2003	Zhang et al.	
SK		US- 6,555,879	4-29-2003	Krivokapic et al.	
SK		US- 2001/0024847 A1	9-27-2001	Snyder	
SK		US- 2002/0030231	3-14-2002	Okawa et al.	
SK		US- 5,361,225	11-01-1994	Takanori	
SC		US- 5,040,034	8-13-1991	Yoshinori et al.	
SK		US- 4,513,309	4-23-1985	Cricchi	
SK		US- 4,554,569	11-19-1985	Tove et al.	
SK		US- 5,250,834	10-05-1993	Nowak	
SK		US- 5,665,993	9-9-1997	Keller et al.	
SK		US- 6,130,750	10-2000	Ausschnitt et al.	

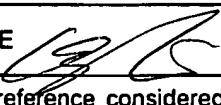
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OTHER DOCUMENTS - NON-PATENT LITERATURE DOCUMENTS

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			YES	NO
SK		LEPSELTHER, M.P., SZE, S.M. <u>SB-IGFET: An Insulated Gate Field Effect Transistor Using Schottky Barrier Contacts for Source and Drain.</u> Proceedings of the IEEE, August 1968; pp. 1400-1402.	<input type="checkbox"/>	<input type="checkbox"/>
SK		LEPSELTHER, M.P., MACRAE, A.U., MACDONALD, R.W. <u>SB-IGFET, II: An Ion Implanted IGFET Using Schottky Barriers.</u> Proceedings of the IEEE, May 1969; pp. 812-813.	<input type="checkbox"/>	<input type="checkbox"/>
SK		KISAKI, Hitoshi. <u>Tunnel Transistor.</u> Proceedings of the IEEE, July 1973; pp. 1053-1054.	<input type="checkbox"/>	<input type="checkbox"/>
SK		KOENEKE, C.J., SZE, S.M., LEVIN, R.M., KINSBRON, E. <u>Schottky MOSFET for VLSI.</u> IEDM, 1981; pp. 367-370.	<input type="checkbox"/>	<input type="checkbox"/>
SK		SUGINO, M., AKERS, L.A., REBESCHINI, M.E. <u>CMOS Latch-Up Elimination Using Schottky Barrier PMOS.</u> IEDM, 1982; pp. 462-465.	<input type="checkbox"/>	<input type="checkbox"/>
SK		KOENEKE, C.J., LYNCH, W.T. <u>Lightly Doped Schottky MOSFET.</u> IEDM, 1982; pp. 466-469.	<input type="checkbox"/>	<input type="checkbox"/>
SK		MOCHIZUKI, T., WISE, K.D. <u>An n-Channel MOSFET with Schottky Source and Drain.</u> IEEE Electron Device Letters, EDL-5, No. 4, April 1984; pp. 108-111.	<input type="checkbox"/>	<input type="checkbox"/>
SK		OH, C.S., KOH, Y.H., KIM, C.K. <u>A New P-Channel MOSFET Structure with Schottky Clamped Source and Drain.</u> IEDM, 1984; pp. 609-612.	<input type="checkbox"/>	<input type="checkbox"/>
SK		SWIRHUN, Stanley E., et al. <u>A VLSI Suitable Schottky Barrier CMOS Process.</u> IEEE Transactions on Electron Devices, ED-32, No. 2, February 1985; pp. 194-202.	<input type="checkbox"/>	<input type="checkbox"/>
SK		TOVE, P.A., BOHLIN, K., MASSZI, F., NORDE, H., NYLANDER, J., TIREN, T., MAGNUSSON, U. <u>Complementary Si MESFET Concept Using Silicon-on-Sapphire Technology.</u> IEEE Electron Device Letters, Vol. 9, No. 1, January 1988; pp. 47-49.	<input type="checkbox"/>	<input type="checkbox"/>
SK		TOVE, P.A., BOHLIN, K.E., NORDE, H., MAGNUSSON, U., TIREN, J., SODERBARG, A., ROSLING, M., MASSZI, F., NYANDER, J. <u>Silicon IC Technology Using Complementary MESFETs.</u> Solid State Devices, Elsevier Science Publishers (North Holland), 1988; pp. 607-609.	<input type="checkbox"/>	<input type="checkbox"/>

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			YES	NO
SK		TSUI, B., CHEN, M. <u>A Novel Process for High-Performance Schottky Barrier PMOS</u> . <i>J. Electrochem Soc.</i> , Vol. 136, No. 5, May 1989; pp. 1456-1459.	<input type="checkbox"/>	<input type="checkbox"/>
SK		MISRA, D., SIMHADRI, V.S. <u>A Survey of the Potential of an IrSi Schottky Barrier MOSFET Based on Simulation Studies</u> . <i>Solid State Electronics</i> , Vol. 35, No. 6, 1992; pp. 829-833.	<input type="checkbox"/>	<input type="checkbox"/>
SK		HATTORI, Reiji, NAKAE, Akihiro, SHIRAFUJI, Junji. <u>A New Type of Tunnel-Effect Transistor Employing Internal Field Emission of Schottky Barrier Junction</u> . <i>Japan J. Appl. Phys.</i> , Vol. 31, 1992; pp. L1467-L1469.	<input type="checkbox"/>	<input type="checkbox"/>
SK		HATTORI, Reiji, SHIRAFUJI, Junji. <u>Numerical Simulation of Tunnel Effect Transistors</u> . <i>Japan J. Appl. Phys.</i> , Vol. 33, 1994; pp. 612-618.	<input type="checkbox"/>	<input type="checkbox"/>
SK		TUCKER, J.R., WANG, C., LYDING, J.W., SHEN, T.C., ABELN, G.C. <u>Nanometer Scale MOSFETs and STM Patterning on Si</u> . <i>SSDM</i> 1994, August 1994; pp. 322-324.	<input type="checkbox"/>	<input type="checkbox"/>
SK		TUCKER, J.R., WANG, C., CARNEY, P.S. <u>Silicon Field-Effect Transistor Based on Quantum Tunneling</u> . <i>Applied Physics Letters</i> , Vol. 65, No. 5, 1 August 1994; pp. 618-620.	<input type="checkbox"/>	<input type="checkbox"/>
SK		KIMURA, Mitsuteru, MATSUDATE, Tadashi. <u>A New Type of Schottky Tunnel Transistor</u> . <i>IEEE Electron Device Letters</i> , EDL-15, No. 10, October 1994, pp. 412-414.	<input type="checkbox"/>	<input type="checkbox"/>
SK		SNYDER, John P., HELMS, C.R., NISHI, Yoshio. <u>Experimental Investigation of a PtSi Source and Drain Field Emission Transistor</u> . <i>Applied Physics Letters</i> , Vol. 67, No. 10, 4 September 1995; pp. 1420-1422.	<input type="checkbox"/>	<input type="checkbox"/>
SK		WOLF, Stanley. <u>Silicon Processing for the VLSI Era</u> . Volume 3: The Submicron MOSFET, Lattice Press, Sunset Beach, CA, 1995; pp. 523-528.	<input type="checkbox"/>	<input type="checkbox"/>
SK		RISHTON, S.A., ISMAIL, K., CHU, J.O., CHAN, K. <u>A MOS Transistor with Schottky Source/Drain Contacts and a Self-Aligned Low-Resistance T-gate</u> . <i>Microelectronics Engineering</i> , Vol. 35, 1997; pp. 361-363.	<input type="checkbox"/>	<input type="checkbox"/>
SK		NISHISAKA, Mika, ASANO, Tanemasa. <u>Reduction of the Floating Body Effect in SOI MOSFETs by Using Schottky Source/Drain Contacts</u> . <i>Japan J. Appl. Phys.</i> , Vol. 37, March 1998; pp. 1295-1299.	<input type="checkbox"/>	<input type="checkbox"/>

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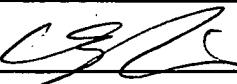
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	TRANSLATION	
			YES	NO
SK		WANG, C., SNYDER, John P., TUCKER, J.R. <u>Sub-50nm PtSi Schottky Source/Drain p-MOSFETs</u> . <i>56th Annual Device Research Conference Digest</i> , June 1998, pp. 72-73.	<input type="checkbox"/>	<input type="checkbox"/>
SK		ZHAO, Q.T., KLINKHAMMER, F., DOLLE, M., KAPPIUS, L., MANTL, S. <u>Nanometer Patterning of Epitaxial CoSi₂/Si(100) for Ultrashort Channel Schottky Barrier Metal-Oxide-Semiconductor Field Effect Transistors</u> . <i>Applied Physics Letters</i> , Vol. 74, No. 3, 18 January 1999; pp. 454-456.	<input type="checkbox"/>	<input type="checkbox"/>
SK		WANG, C., SNYDER, John P., TUCKER, J.R. <u>Sub-40nm PtSi Schottky Source-Drain Metal-Oxide-Semiconductor Field-Effect-Transistors</u> . <i>Applied Physics Letters</i> , Vol. 74, No. 8, 22 February 1999; pp. 1174-1176.	<input type="checkbox"/>	<input type="checkbox"/>
SK		SNYDER, John P., HOLMS, C.R., NISHI, Yoshio. <u>Analysis of the Potential Distribution in the Channel Region of a Platinum Silicided Source/Drain Metal Oxide Semiconductor Field Effect Transistor</u> . <i>Applied Physics Letters</i> , Vol. 74, No. 22, 31 May 1999; pp. 3407-3409.	<input type="checkbox"/>	<input type="checkbox"/>
SK		SAITO, W., YAMAGAMI, S., ITOH, A., ASADA, M. <u>35nm Metal Gate SOI-p-MOSFETs with PtSi Schottky Source/Drain</u> . <i>57th Annual Device Research Conference Digest</i> , June 1999; pp. 30-31.	<input type="checkbox"/>	<input type="checkbox"/>
SK		TUCKER, J.R. <u>Schottky Barrier MOSFETs for Silicon Nano-electronics</u> . <i>IEEE Frontiers in Electronics</i> , January 1997; pp. 97-100.	<input type="checkbox"/>	<input type="checkbox"/>
SK		LAPLANTE, Philip A. (Editor-in-Chief). <u>Comprehensive Dictionary of Electrical Engineering</u> . IEEE Press, 1999, page 97.	<input type="checkbox"/>	<input type="checkbox"/>
SK		MULLER, Richard S. and KAMINS, Theodore I. <u>Device Electronics for Integrated Circuit</u> . John Wiley & Sons, Second Edition, 1977, 1986, pp. 448, 505-511.	<input type="checkbox"/>	<input type="checkbox"/>
SK		PIERRET, Modular Series On Solid State Devices, vol. I Semiconductor Fundamentals, Addison-Wesley, 1983; pp. 29-33.	<input type="checkbox"/>	<input type="checkbox"/>
SK		NEUDECK, Gerold W. <u>Volume II: The PN Junction Diode</u> , Modular Series On Solid State Devices. Addison-Wesley, 1983; pp. 8-10.	<input type="checkbox"/>	<input type="checkbox"/>
SK		On-line Encyclopedia Britannica, 2001, definition of "rare-earth element.", date not established; 2 pages.	<input type="checkbox"/>	<input type="checkbox"/>

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						YES	NO
SK		SZE, S.M. <u>Physics of Semiconductor Devices</u> , John Wiley & Sons, Second Edition, 1981; pp. 293-294.				<input type="checkbox"/>	<input type="checkbox"/>
SK		CALVET, L. E., LUEBBEN, H., REED, M.A., WANG, C., SNYDER, J.P., and TUCKER, J.R. <u>Subthreshold and scaling of PtSi Schottky barrier MOSFETs</u> , 2000 Academic Press, <u>Superlattices and Microstructures</u> , Vol. 28, No. 5/6; pp. 501-506.				<input type="checkbox"/>	<input type="checkbox"/>
SK		WOLF, Stanley. <u>Silicon Processing for the VLSI Era</u> , Vol. 3: <u>The Submicron MOSFET</u> . Lattice Press, 1995; pp. 183-187.				<input type="checkbox"/>	<input type="checkbox"/>
SK		Web page "provided by Laurie Calvet", "Device Physics of the SBMOSFET", http://www.eng.yale.edu/reedlab/research/semicond.html , date not established; 7 pages.				<input type="checkbox"/>	<input type="checkbox"/>
SK		WINSTEAD, B. and RAVAIOLI, U. <u>Simulation of Schottky Barrier MOSFET's with a Coupled Quantum Injection/Monte Carlo Technique</u> . <u>IEEE Transactions on Electron Device</u> , Vol. 47, No. 6, June 2000; pp. 1241-1246.				<input type="checkbox"/>	<input type="checkbox"/>
SK		GANG, D., XIAOYAN, L., LEI, S., JIAPING, Y., RUQI, H., HOULET, P., and FUJITAN, H. <u>Monte Carlo Simulation of 50nm n-Channel Schottky Barrier Tunneling Transistors</u> . <u>Chinese Journal of Electronics</u> , Vol. 11, No. 2, April 2002; pp. 200-203.				<input type="checkbox"/>	<input type="checkbox"/>
SK		RISHTON, S.A., ISMAIL, K., CHU, J.O., CHAN, K.K., LEE, K.Y. <u>New Complimentary metal-oxide semiconductor technology with self-aligned Schottky source/drain and low-resistance T gates</u> . <u>J. Vac. Sci. Technol. B</u> , 15(6), Nov/Dec 1997, pp. 2795-2798.				<input type="checkbox"/>	<input type="checkbox"/>
SK		KEDZIERSKI, J., XUAN, P., SUBRAMANIAN, V., BOKOR, J., KING, T-J., HU, C., ANDERSON, E. <u>A 20 nm gate-length ultra-thin body p-MOSFET with silicide source/drain</u> . <u>Superlattices and Microstructures</u> , Vol. 28, No. 5/6, 2000, pp. 445-452.				<input type="checkbox"/>	<input type="checkbox"/>
SK		Magnusson, U. et al., <u>Bulk Silicon Technology For Complementary MESFETs</u> . <u>Electronics Letters</u> , Vol. 25, No. 9, April 27, 1989; pps. 565-566.				<input type="checkbox"/>	<input type="checkbox"/>
SK		Random House College Dictionary, 1980, Random House, Inc., Revised Ed., pages 17 and 1066.				<input type="checkbox"/>	<input type="checkbox"/>
SK		International Technology Roadmap for Semiconductors 1999, US Copyright 1999 by Semiconductor Industry Association, Front End Processes section, page 107.				<input type="checkbox"/>	<input type="checkbox"/>
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SK		S.M. Sze, <u>Physics of Semiconductor Devices</u> , 1981, John Wiley & Sons., Second Edition, pp. 451-453.	<input type="checkbox"/>	<input type="checkbox"/>
SK		Tu, K.N. Thompson, R.D., Tsaur, B.Y. <u>Low Schottky Barrier of Rare-Earth Silicide on n-Si</u> , <i>Applied Physics Letters</i> , vol. 38, No. 8, Apr. 1981; pp. 626-628.	<input type="checkbox"/>	<input type="checkbox"/>
SK		Unewisse, M.H., Storey, J.W. V. <u>Electrical and Infared Investigation of Erbium Silicide</u> , <i>J. Appl. Phys.</i> , vol. 72, No. 6., Sep. 1992; pp. 2367-2371.	<input type="checkbox"/>	<input type="checkbox"/>
SK		Geppert, Linda. <u>The 100-Million Transistor IC</u> . <i>IEEE Spectrum</i> , Jul. 1999; pp. 23-24.	<input type="checkbox"/>	<input type="checkbox"/>
SK		Taur, Yuan. <u>The Incredible Shrinking Transistor</u> . <i>IEEE Spectrum</i> , Jul. 1999; pp. 25-29.	<input type="checkbox"/>	<input type="checkbox"/>
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